May 2017

SemiHow
Know-How for Semiconductor

HFI6N90 / HFW6N90
900V N-Channel MOSFET

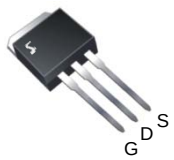
Features

- ❑ Superior Avalanche Rugged Technology
- ❑ Robust Gate Oxide Technology
- ❑ Very Low Intrinsic Capacitances
- ❑ Excellent Switching Characteristics
- ❑ 100% Avalanche Tested
- ❑ RoHS Compliant

Key Parameters

Parameter	Value	Unit
BV_{DSS}	900	V
I_D	6	A
$R_{DS(on),\ Typ}$	1.95	Ω
$Qg_{,\ Typ}$	41	nC

HFI6N90
TO-262



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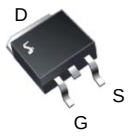
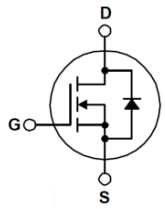


Symbol



Absolute Maximum Ratings

T_C=25℃ unless otherwise specified

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-Source Voltage	900	V
I_D	Drain Current - Continuous (T_C = 25℃)	6.0	A
	Drain Current - Continuous (T_C = 100℃)	3.8	A
I_{DM}	Drain Current - Pulsed (Note 1)	24	A
V_{GS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	650	mJ
I_{AR}	Avalanche Current (Note 1)	6.0	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	16.7	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Power Dissipation (T_A = 25℃)*	3.13	W
	Power Dissipation (T_C = 25℃)	167	W
	- Derate above 25℃	1.33	W/℃
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	℃
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	℃

Thermal Resistance Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Junction-to-Case, Max.	0.75	℃/W
$R_{\theta JA}$	Junction-to-Ambient (minimum pad of 2 oz copper), Max.	62.5	℃/W
$R_{\theta JA}$	Junction-to-Ambient (* 1 in^2 pad of 2 oz copper), Max.	40	℃/W

Electrical Characteristics T_J=25 °C unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
On Characteristics						
V_{GS}	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	2.0	--	4.0	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 3 A	--	1.95	2.4	Ω
g_{FS}	Forward Transconductance	V_{DS} = 50 V, I_D = 3 A	--	5	--	S
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	900	--	--	V
$\triangle BV_{DSS}$ /$\triangle T_J$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25℃	--	0.8	--	V/℃
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 900 V, V_{GS} = 0	--	--	10	μA
		V_{DS} = 720 V, T_C = 125℃	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS} = ±30 V, V_{DS} = 0 V	--	--	±100	nA
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	1500	1950	pF
C_{oss}	Output Capacitance		--	115	150	pF
C_{rss}	Reverse Transfer Capacitance		--	20	26	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Time	V_{DS} = 450 V, I_D = 6 A, R_G = 25 Ω (Note 4,5)	--	43	96	ns
t_r	Turn-On Rise Time		--	36	82	ns
$t_{d(off)}$	Turn-Off Delay Time		--	142	294	ns
t_f	Turn-Off Fall Time		--	33	76	ns
Q_g	Total Gate Charge	V_{DS} = 720 V, I_D = 6 A, V_{GS} = 10 V (Note 4,5)	--	41	53	nC
Q_{gs}	Gate-Source Charge		--	8	--	nC
Q_{gd}	Gate-Drain Charge		--	18	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	6	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	24	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 6 A	--	--	1.4	V
trr	Reverse Recovery Time	V_{GS} = 0 V, I_S = 6 A, di_F/dt = 100 A/μs	--	780	--	ns
Qrr	Reverse Recovery Charge		--	9.0	--	μC

Notes :

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L=34mH, I_{AS}=6A, V_{DD}=50V, R_G=25Ω, Starting T_J=25°C
3. I_{SD}≤6A, di/dt≤200A/μs, V_{DD}≤BV_{DSS} , Starting T_J=25 °C
4. Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature

Typical Characteristics

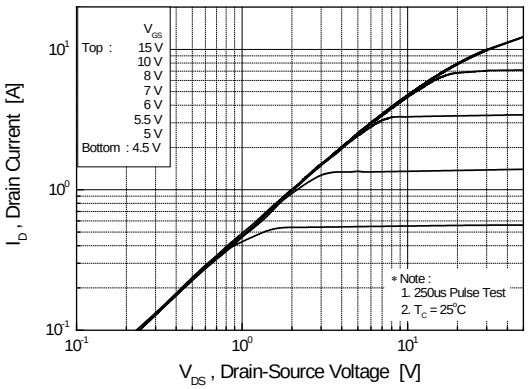


Figure 1. On Region Characteristics

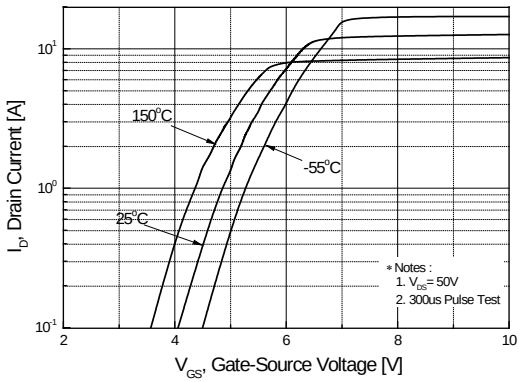


Figure 2. Transfer Characteristics

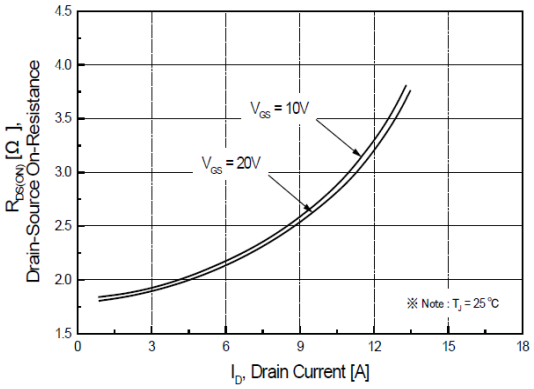


Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

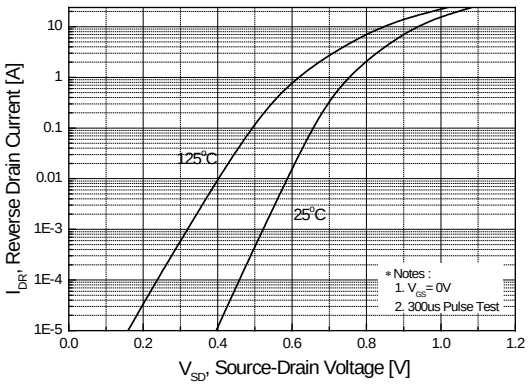


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

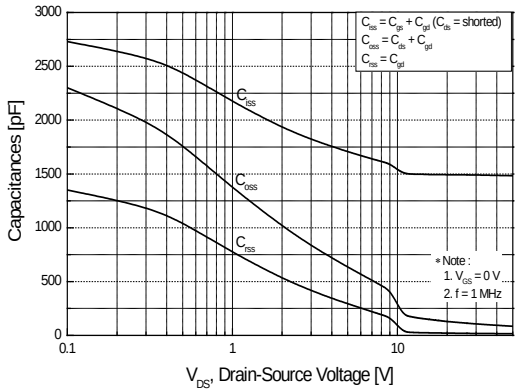


Figure 5. Capacitance Characteristics

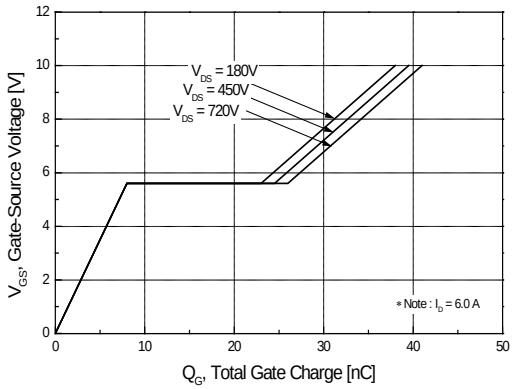


Figure 6. Gate Charge Characteristics

Typical Characteristics (continued)

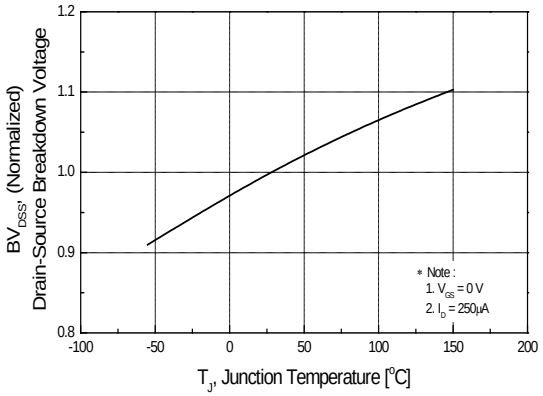


Figure 7. Breakdown Voltage Variation vs Temperature

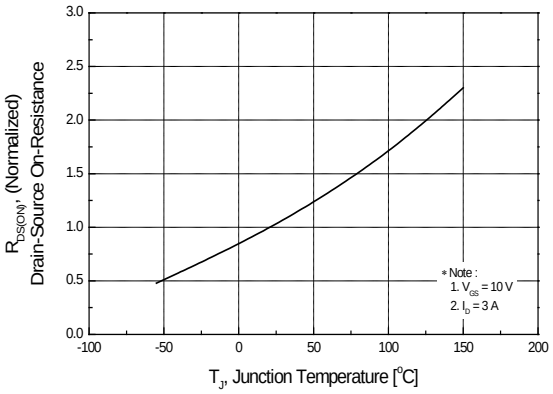


Figure 8. On-Resistance Variation vs Temperature

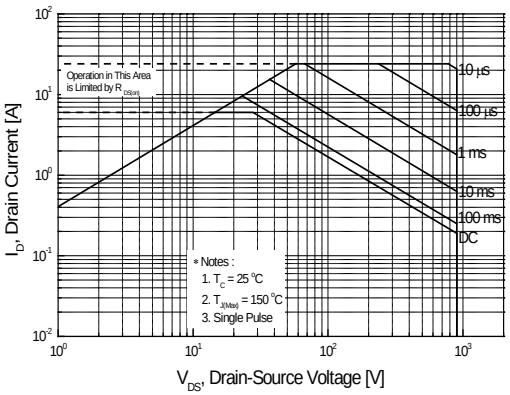


Figure 9. Maximum Safe Operating Area

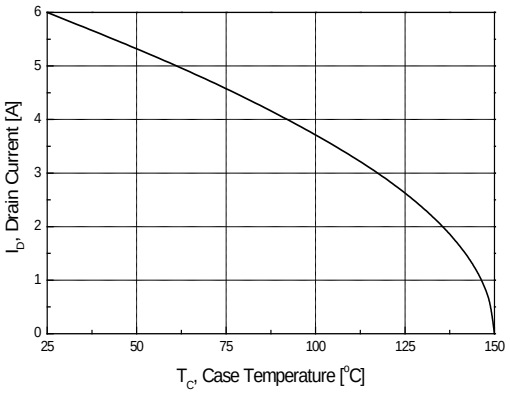


Figure 10. Maximum Drain Current vs Case Temperature

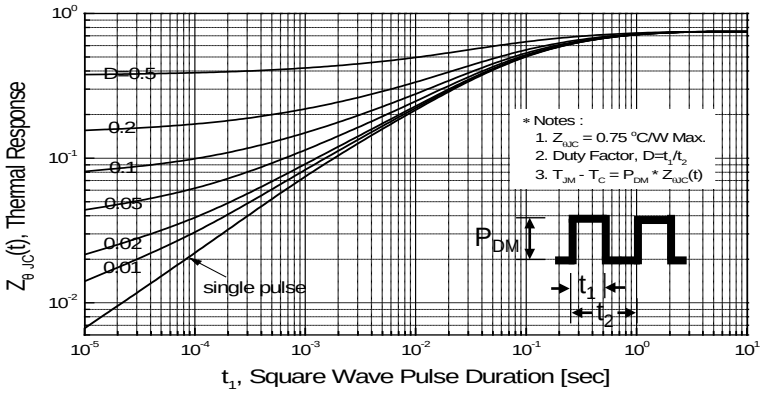


Figure 11. Transient Thermal Response Curve

Fig 12. Gate Charge Test Circuit & Waveform

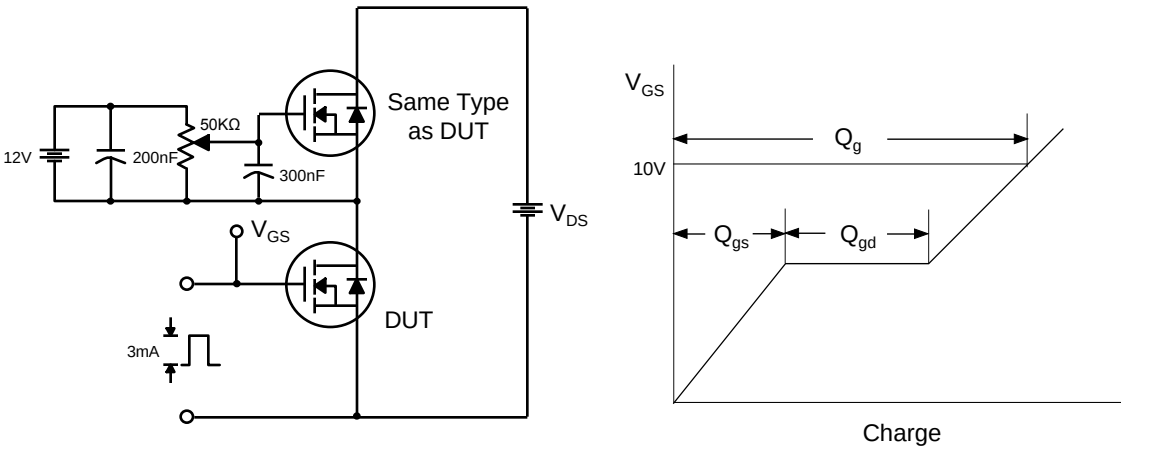


Fig 13. Resistive Switching Test Circuit & Waveforms

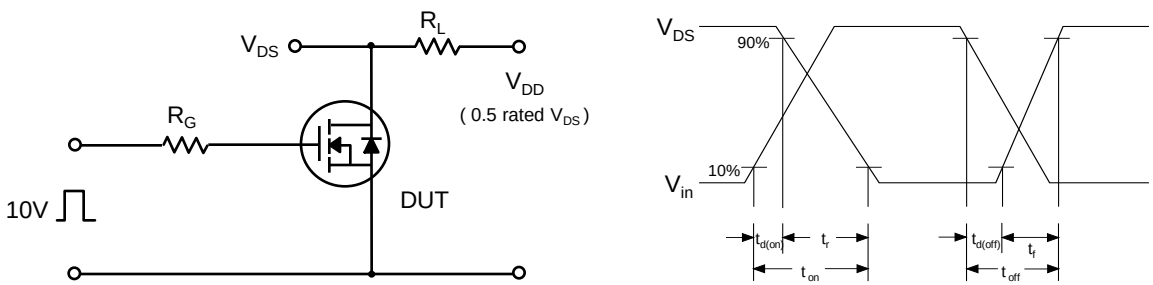


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

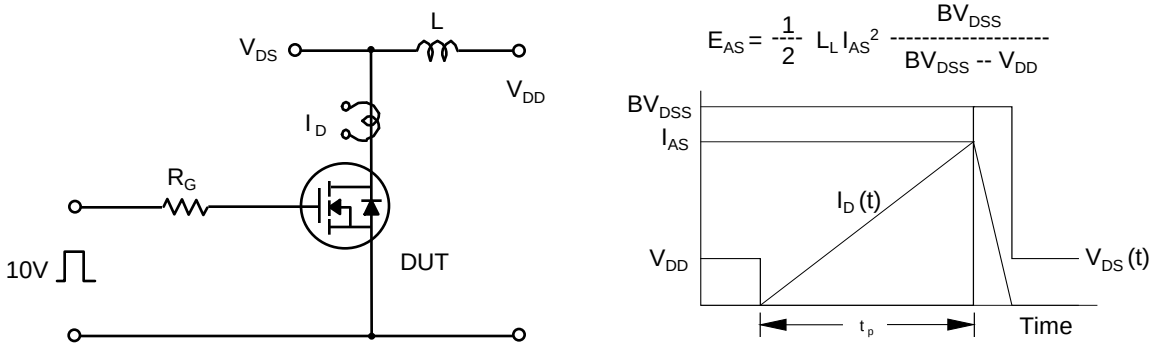
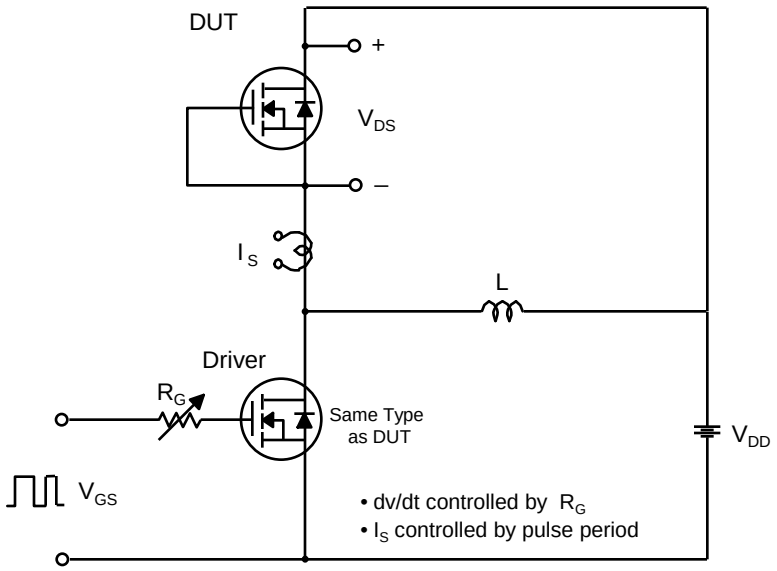
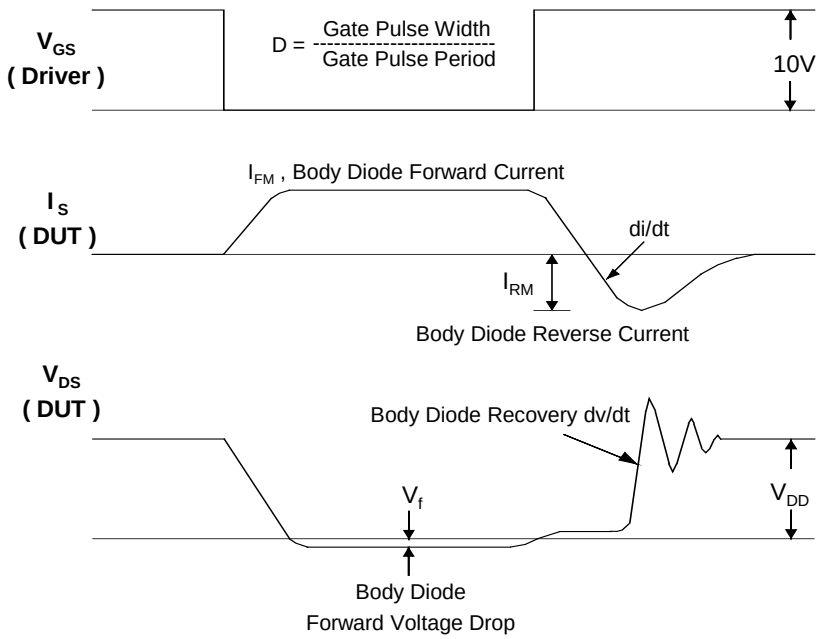


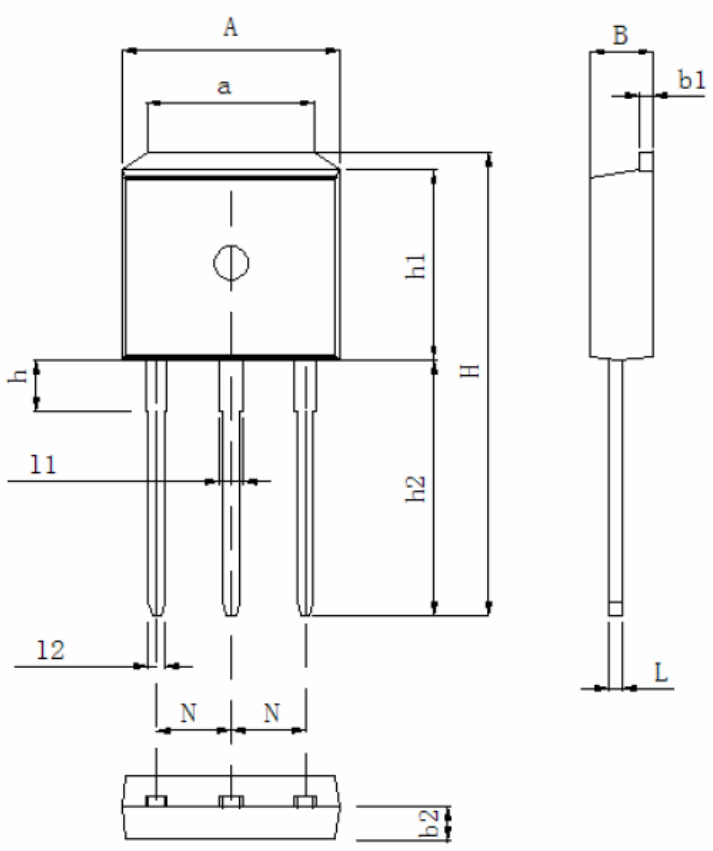
Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





Package Dimension

I²-PAK
(TO-262)

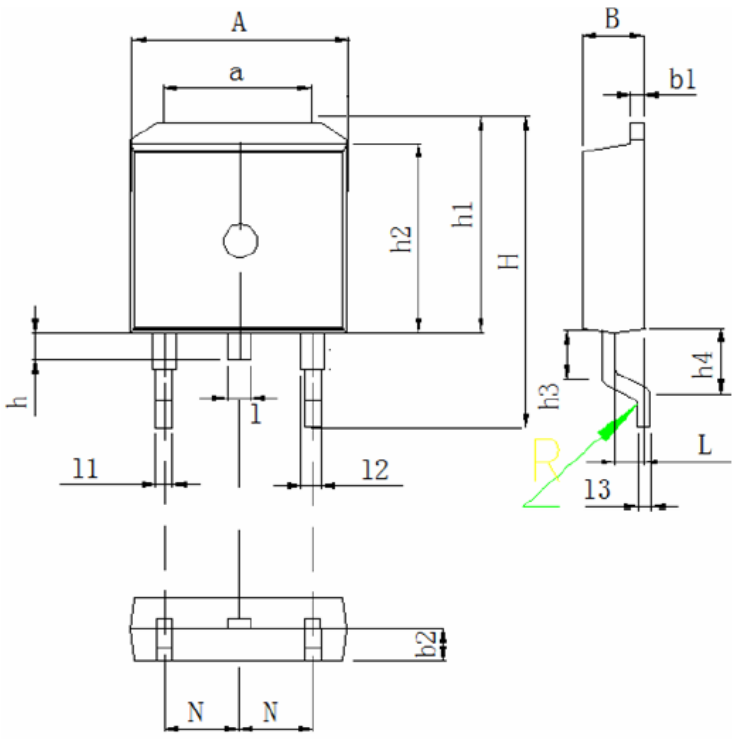


DIM	MILLIMETERS
A	9.8±0.2
a	7.4±0.2
B	4.5±0.2
b1	1.3±0.05
b2	2.4±0.2
H	24.2±0.3
h	3.1±0.2
h1	10.5±0.2
h2	13.2±0.2
L	0.5±0.1
l1	1.3±0.1
l2	0.8±0.1
N	2.45

Unit :mm

Package Dimension

D²-PAK
(TO-263)



DIM	MILLIMETERS
A	9.8±0.2
a	7.4±0.2
B	4.5±0.2
b1	1.3±0.05
b2	2.4±0.2
H	15.5±0.3
h	1.54±0.2
h1	10.5±0.2
h2	9.2±0.1
h3	1.54±0.2
h4	2.7±0.2
L	2.4±0.2
l	1.3±0.1
l1	0.8±0.1
l2	1.3±0.1
l3	0.5±0.1
N	2.45±0.05
R	0.5R±0.05

Unit :mm